



ELECTRONICS, INC.
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NTE5563 Silicon Controlled Rectifier (SCR) 1880 Amp

Absolute Maximum Ratings: ($T_J = +125^\circ\text{C}$ unless otherwise specified)

Repetitive Peak Voltages, V_{RRM} , V_{DRM} , V_{DSM}	1600V
Non-Repetitive Peak Reverse Blocking Voltage,	1700V
Average On-State Current (Half Sine Wave), $I_{T(AV)}$	
$T_{hs} = +55^\circ\text{C}$ (Double Side Cooled)	1400A
$T_{hs} = +85^\circ\text{C}$ (Single Side Cooled)	550A
RMS On-State Current ($T_{hs} = +25^\circ\text{C}$, Double Side Cooled), $I_{T(RMS)}$	2840A
Continuous On-State Current ($T_{hs} = +25^\circ\text{C}$, Double Side Cooled), I_T	2400A
Peak One-Cycle Surge (10ms duration, 60% V_{RRM} re-applied), $I_{TSM(1)}$	20500A
Non-Repetitive On-State Current (10ms duration, $V_R \leq 10V$), $I_{TSM(2)}$	22550A
Maximum Permissible Surge Energy ($V_R \leq 10V$), I^2t	
10ms duration	2500000A ² s
3ms duration	1890000A ² s
Peak Forward Gate Current (Anode positive with respect to cathode), I_{FGM}	20A
Peak Forward Gate Voltage (Anode positive with respect to cathode), V_{FGM}	22V
Peak Reverse Gate Voltage, V_{RGM}	5V
Average Gate Power, P_G	4W
Peak Gate Power (100 μ s pulse width), P_{GM}	120W
Rate of Rise of Off-State Voltage (To 80% V_{DRM} gate open-circuit), dv/dt	200V/ μ s
Rate of Rise of On-State Current, di/dt	
(Gate drive 20V, 20 Ω with $t_r \leq 1\mu$ s, anode voltage $\leq 80\%$ V_{DRM})	
Repetitive	500A/ μ s
Non-Repetitive	1000A/ μ s
Operating Temperature Range, T_{hs}	-40° to +125°C
Storage Temperature Range, T_{stg}	-40° to +150°C
Thermal Resistance, Junction-to-Heatsink, $R_{th(j-hs)}$	
(For a device with a maximum forward voltage drop characteristic)	
Double Side Cooled	0.03°C/W
Single Side Cooled	0.06°C/W
Peak On-State Voltage ($I_{TM} = 2550A$), V_{TM}	1.41V
Forward Conduction Threshold Voltage, V_O	0.965V
Forward Conduction Slope Resistance, r	0.174m Ω

Absolute Maximum Ratings (Cont'd): ($T_J = +125^\circ\text{C}$ unless otherwise specified)

Repetitive Peak Off-State Current (At V_{DRM}), I_{DRM}	100mA
Repetitive Peak Reverse Current (At V_{RRM}), I_{RRM}	100mA
Maximum Gate Current ($V_A = 6\text{V}$, $I_A = 2\text{A}$, $T_J = +25^\circ\text{C}$), I_{GT}	300mA
Maximum Gate Voltage ($V_A = 6\text{V}$, $I_A = 2\text{A}$, $T_J = +25^\circ\text{C}$), V_{GT}	3V
Maximum Holding Current ($V_A = 6\text{V}$, $I_A = 2\text{A}$, $T_J = +25^\circ\text{C}$), I_{H}	1A
Maximum Gate Voltage Which Will Not Trigger Any Device, V_{GD}	0.25V

